

Please add the following new claims:

--11. (New) An electric semiconductor component, comprising:
a monocrystalline semiconductor substrate;
an insulation layer arranged on a surface of the semiconductor substrate and
penetrated by at least one contact hole in at least one location; and
a contact structure that contacts the semiconductor substrate through the contact hole
and made of a material in which a semiconductor material of the semiconductor substrate is
soluble in an anisotropic dissolving process;
wherein edges of the contact hole include diffusion stop structures.

12. (New) The semiconductor component according to claim 11, wherein the
diffusion stop structures include curved segments.

13. (New) The semiconductor component according to claim 12, wherein the contact
hole is shaped one of circular and as overlapping intersecting circles.

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14. (New) The semiconductor component according to claim 11, wherein the diffusion stop structures include microstructured sections of the edges.

15. (New) The semiconductor component according to claim 14, wherein the
microstructured sections include one of a crenellated and a sawtooth pattern.

16. (New) The semiconductor component according to claim 15, wherein the one of
the crenellated and the sawtooth pattern includes a plurality of projections, each projection
having an edge length of at most 2 μ m.

17. (New) The semiconductor component according to claim 11, wherein the
semiconductor material includes at least one class of crystal planes that is subject to one of
little and no attack in the dissolving process, and the diffusion stop structures include
rectilinear sections of the edges intersecting the crystal planes of the class of crystal planes
extending in the semiconductor substrate beneath the contact hole.